



28C16A

16K (2K x 8) CMOS EEPROM

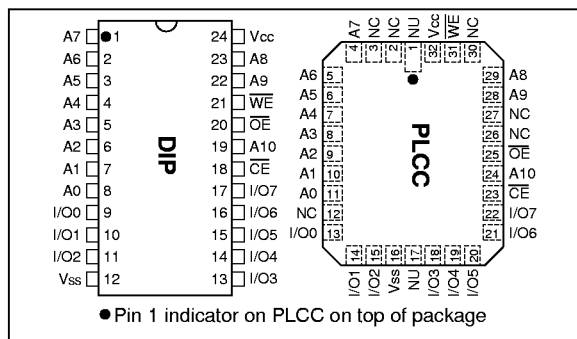
FEATURES

- Fast Read Access Time—150 ns
- CMOS Technology for Low Power Dissipation
 - 30 mA Active
 - 100 μ A Standby
- Fast Byte Write Time—200 μ s or 1 ms
- Data Retention >200 years
- High Endurance - Minimum 10^4 Erase/Write Cycles
- Automatic Write Operation
 - Internal Control Timer
 - Auto-Clear Before Write Operation
 - On-Chip Address and Data Latches
- Data polling
- Chip Clear Operation
- Enhanced Data Protection
 - VCC Detector
 - Pulse Filter
 - Write Inhibit
- Electronic Signature for Device Identification
- 5-Volt-Only Operation
- Organized 2Kx8 JEDEC Standard Pinout
- 24-pin Dual-In-Line Package
- 32-pin PLCC Package
- Available for Extended Temperature Ranges:
 - Commercial: 0°C to +70°C
 - Industrial: -40°C to +85°C

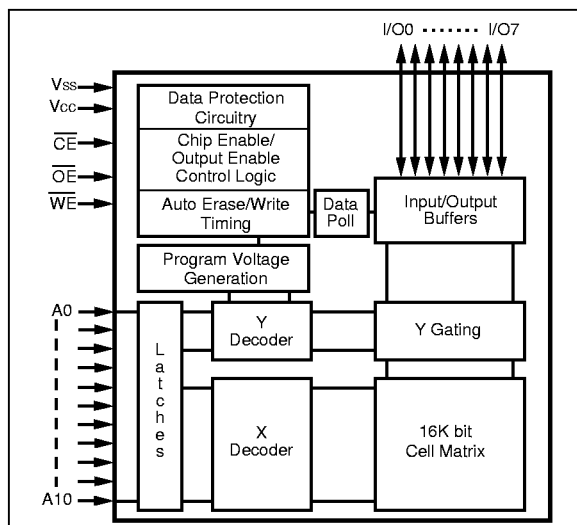
DESCRIPTION

The Microchip Technology Inc. 28C16A is a CMOS 16K non-volatile electrically Erasable PROM. The 28C16A is accessed like a static RAM for the read or write cycles without the need of external components. During a "byte write", the address and data are latched internally, freeing the microprocessor address and data bus for other operations. Following the initiation of write cycle, the device will go to a busy state and automatically clear and write the latched data using an internal control timer. To determine when a write cycle is complete, the 28C16A uses $\overline{\text{Data}}$ polling. $\overline{\text{Data}}$ polling allows the user to read the location last written to when the write operation is complete. CMOS design and processing enables this part to be used in systems where reduced power consumption and reliability are required. A complete family of packages is offered to provide the utmost flexibility in applications.

PACKAGE TYPES



BLOCK DIAGRAM



1.0 ELECTRICAL CHARACTERISTICS

1.1 MAXIMUM RATINGS*

VCC and input voltages w.r.t. VSS -0.6V to + 6.25V
 Voltage on \overline{OE} w.r.t. VSS -0.6V to +13.5V
 Voltage on A9 w.r.t. VSS -0.6V to +13.5V
 Output Voltage w.r.t. VSS -0.6V to VCC+0.6V
 Storage temperature -65°C to +125°C
 Ambient temp. with power applied -50°C to +95°C

***Notice:** Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

TABLE 1-1: PIN FUNCTION TABLE

Name	Function
A0 - A10	Address Inputs
\overline{CE}	Chip Enable
\overline{OE}	Output Enable
\overline{WE}	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
VCC	+5V Power Supply
VSS	Ground
NC	No Connect; No Internal Connection
NU	Not Used; No External Connection is Allowed

TABLE 1-2: READ/WRITE OPERATION DC CHARACTERISTICS

VCC = +5V ±10% Commercial (C): Tamb = 0°C to +70°C Industrial (I): Tamb = -40°C to +85°C						
Parameter	Status	Symbol	Min	Max	Units	Conditions
Input Voltages	Logic '1' Logic '0'	V _{IH} V _{IL}	2.0 -0.1	VCC+1 0.8	V V	
Input Leakage	—	I _{LI}	-10	10	μA	V _{IN} = -0.1V to VCC+1
Input Capacitance	—	C _{IN}	—	10	pF	V _{IN} = 0V; Tamb = 25°C; f = 1 MHz
Output Voltages	Logic '1' Logic '0'	V _{OH} V _{OL}	2.4	0.45	V V	I _{OH} = -400μA I _{OL} = 2.1 mA
Output Leakage	—	I _{LO}	-10	10	μA	V _{OUT} = -0.1V to VCC+0.1V
Output Capacitance	—	C _{OUT}	—	12	pF	V _{IN} = 0V; Tamb = 25°C; f = 1 MHz
Power Supply Current, Active	TTL input	I _{CC}	—	30	mA	f = 5 MHz (Note 1) VCC = 5.5V;
Power Supply Current, Standby	TTL input TTL input CMOS input	I _{CC} (S)TTL I _{CC} (S)TTL I _{CC} (S)CMOS	—	2 3 100	mA mA μA	\overline{CE} = V _{IH} (0°C to +70°C) \overline{CE} = V _{IH} (-40°C to +85°C) \overline{CE} = VCC-0.3 to VCC+1 \overline{OE} = VCC Other inputs equal VCC or VSS

Note 1: AC power supply current above 5 MHz; 1 mA/MHz.

TABLE 1-3: READ OPERATION AC CHARACTERISTICS

		AC Testing Waveform:		V _{IH} = 2.4V; V _{IL} = 0.45V; V _{OH} = 2.0V; V _{OL} = 0.8V					
		Output Load:		1 TTL Load + 100pF					
		Input Rise and Fall Times:		20 ns					
		Ambient Temperature:		Commercial (C): T _{amb} = 0°C to +70°C Industrial (I): T _{amb} = -40°C to +85°C					
Parameter	Sym	28C16A-15		28C16A-20		28C16A-25		Units	Conditions
		Min	Max	Min	Max	Min	Max		
Address to Output Delay	t _{ACC}	—	150	—	200	—	250	ns	$\overline{OE} = \overline{CE} = V_{IL}$
\overline{CE} to Output Delay	t _{CE}	—	150	—	200	—	250	ns	$\overline{OE} = V_{IL}$
\overline{OE} to Output Delay	t _{OE}	—	70	—	80	—	100	ns	$\overline{CE} = V_{IL}$
\overline{CE} or \overline{OE} High to Output Float	t _{OFF}	0	50	0	55	0	70	ns	
Output Hold from \overline{CE} or \overline{OE} , whichever occurs first	t _{OH}	0	—	0	—	0	—	ns	
Endurance	—	1M	—	1M	—	1M	—	cycles	25°C, V _{CC} = 5.0V, Block Mode (Note)

Note: This parameter is not tested but guaranteed by characterization. For endurance estimates in a specific application, please consult the Total Endurance Model which can be obtained on our BBS or website.

FIGURE 1-1: READ WAVEFORMS

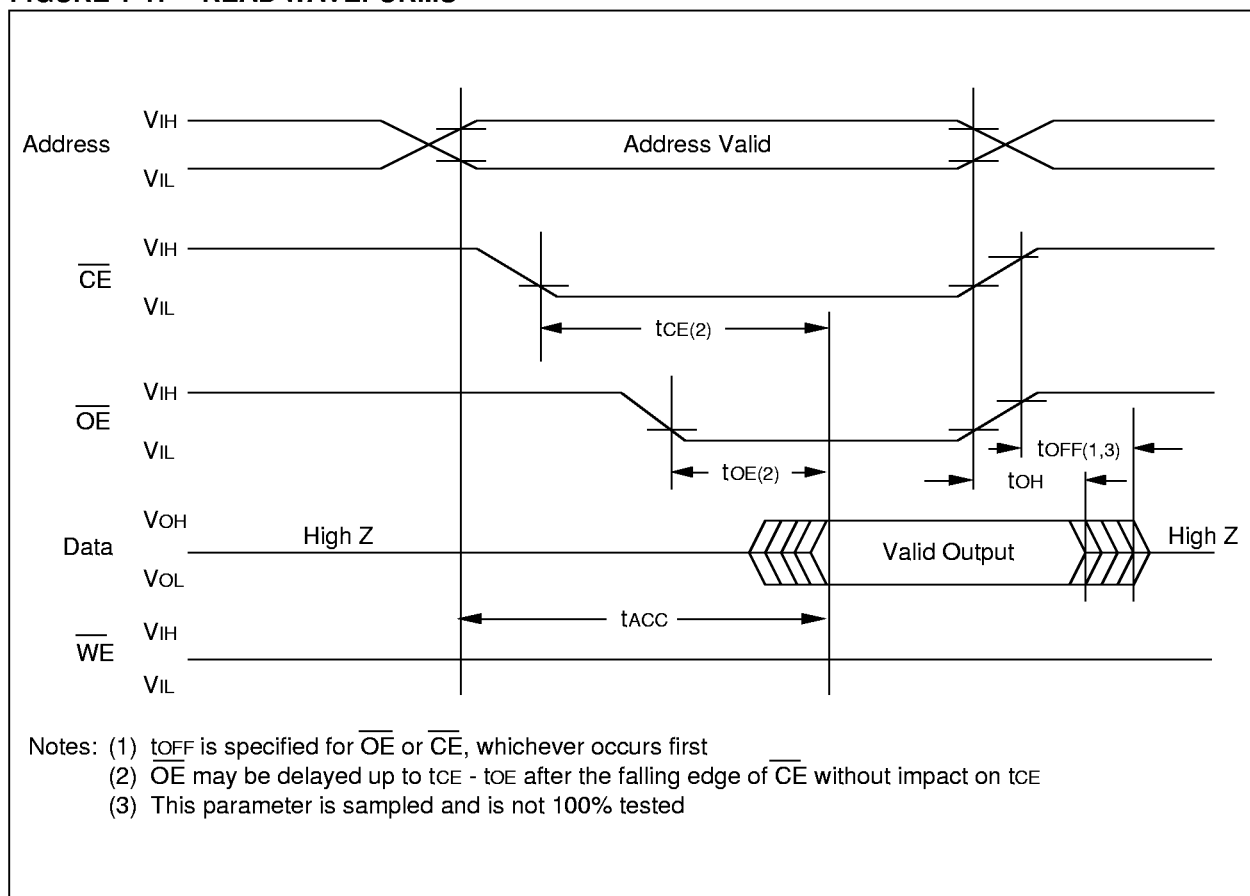


TABLE 1-4: BYTE WRITE AC CHARACTERISTICS

		AC Testing Waveform:		$V_{IH} = 2.4V$ and $V_{IL} = 0.45V$; $V_{OH} = 2.0V$; $V_{OL} = 0.8V$	
		Output Load:		1 TTL Load + 100 pF	
		Input Rise/Fall Times:		20 ns	
		Ambient Temperature:		Commercial (C):	$T_{amb} = 0^{\circ}C$ to $+70^{\circ}C$
				Industrial (I):	$T_{amb} = -40^{\circ}C$ to $+85^{\circ}C$
Parameter	Symbol	Min	Max	Units	Remarks
Address Set-Up Time	t_{AS}	10	—	ns	
Address Hold Time	t_{AH}	50	—	ns	
Data Set-Up Time	t_{DS}	50	—	ns	
Data Hold Time	t_{DH}	10	—	ns	
Write Pulse Width	t_{WPL}	100	—	ns	Note 1
Write Pulse High Time	t_{WPH}	50	—	ns	
\overline{OE} Hold Time	t_{OEH}	10	—	ns	
\overline{OE} Set-Up Time	t_{OES}	10	—	ns	
Data Valid Time	t_{DV}	—	1000	ns	Note 2
Write Cycle Time (28C16A)	t_{WC}	—	1	ms	0.5 ms typical
Write Cycle Time (28C16AF)	t_{WC}	—	200	μs	100 μs typical

Note 1: A write cycle can be initiated by \overline{CE} or \overline{WE} going low, whichever occurs last. The data is latched on the positive edge of \overline{CE} or \overline{WE} , whichever occurs first.

2: Data must be valid within 1000ns max. after a write cycle is initiated and must be stable at least until t_{DH} after the positive edge of \overline{WE} or \overline{CE} , whichever occurs first.

FIGURE 1-2: PROGRAMMING WAVEFORMS

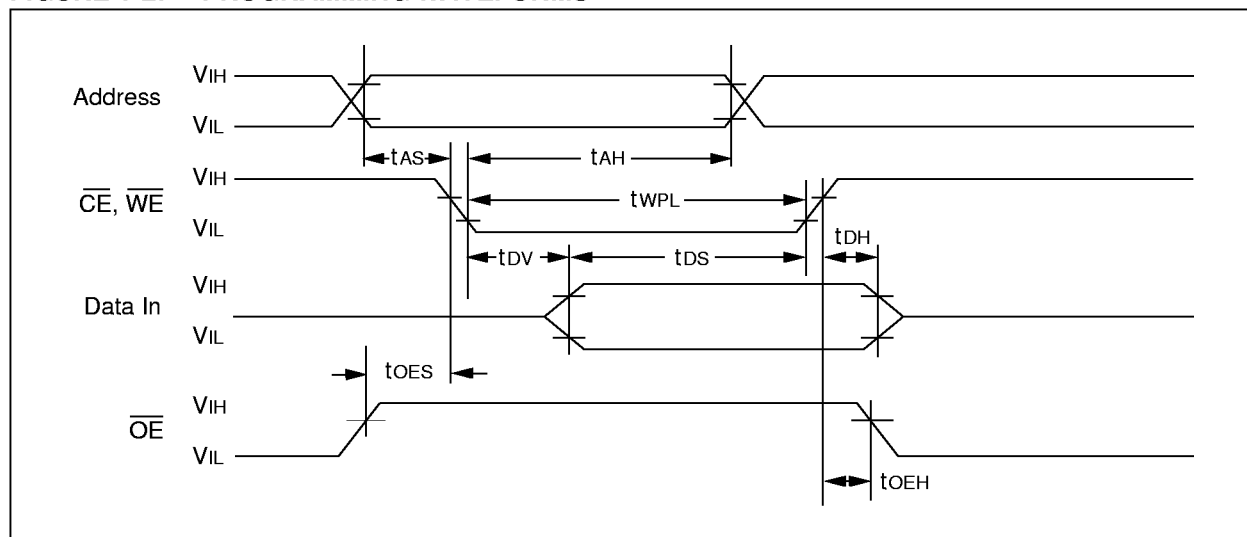


FIGURE 1-3: DATA POLLING WAVEFORMS

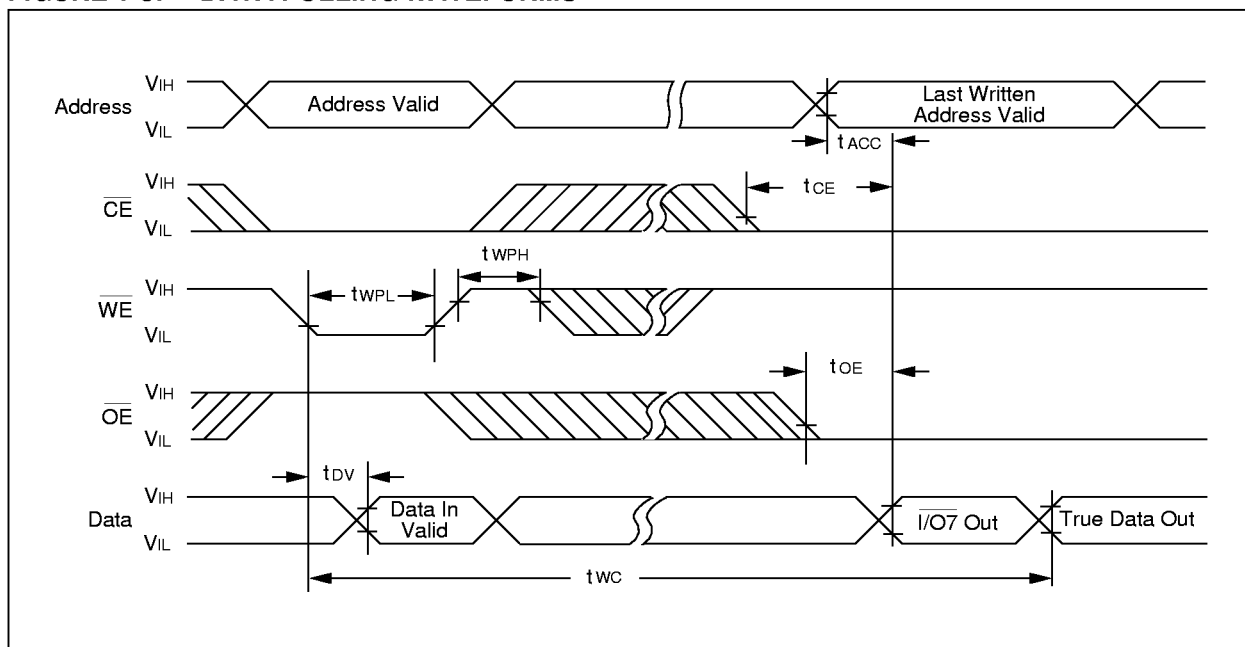


FIGURE 1-4: CHIP CLEAR WAVEFORMS

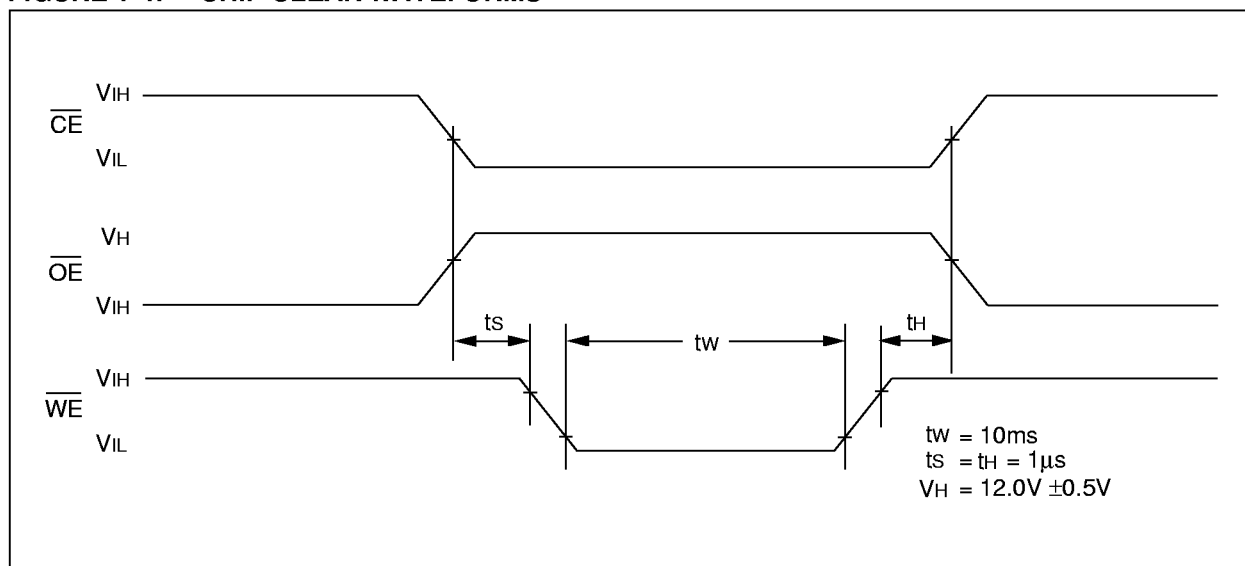


TABLE 1-5: SUPPLEMENTARY CONTROL

Mode	\overline{CE}	\overline{OE}	\overline{WE}	A9	Vcc	I/O
Chip Clear	VIL	VH	VIL	X	Vcc	
Extra Row Read	VIL	VIL	VH	A9 = VH	Vcc	Data Out
Extra Row Write	*	VH	*	A9 = VH	Vcc	Data In

Note 1: $V_H = 12.0\text{V} \pm 0.5\text{V}$ * Pulsed per programming waveforms.

2.0 DEVICE OPERATION

The Microchip Technology Inc. 28C16A has four basic modes of operation—read, standby, write inhibit, and byte write—as outlined in the following table.

Operation Mode	\overline{CE}	\overline{OE}	\overline{WE}	I/O
Read	L	L	H	DOUT
Standby	H	X	X	High Z
Write Inhibit	H	X	X	High Z
Write Inhibit	X	L	X	High Z
Write Inhibit	X	X	H	High Z
Byte Write	L	H	L	DIN
Byte Clear	Automatic Before Each "Write"			

X = Any TTL level.

2.1 Read Mode

The 28C16A has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip enable (\overline{CE}) is the power control and should be used for device selection. Output Enable (\overline{OE}) is the output control and is used to gate data to the output pins independent of device selection. Assuming that addresses are stable, address access time (t_{ACC}) is equal to the delay from \overline{CE} to output (t_{CE}). Data is available at the output t_{OE} after the falling edge of \overline{OE} , assuming that \overline{CE} has been low and addresses have been stable for at least $t_{ACC}-t_{OE}$.

2.2 Standby Mode

The 28C16A is placed in the standby mode by applying a high signal to the \overline{CE} input. When in the standby mode, the outputs are in a high impedance state, independent of the \overline{OE} input.

2.3 Data Protection

In order to ensure data integrity, especially during critical power-up and power-down transitions, the following enhanced data protection circuits are incorporated:

First, an internal V_{CC} detect (3.3 volts typical) will inhibit the initiation of non-volatile programming operation when V_{CC} is less than the V_{CC} detect circuit trip.

Second, there is a \overline{WE} filtering circuit that prevents \overline{WE} pulses of less than 10 ns duration from initiating a write cycle.

Third, holding \overline{WE} or \overline{CE} high or \overline{OE} low, inhibits a write cycle during power-on and power-off (V_{CC}).

2.4 Write Mode

The 28C16A has a write cycle similar to that of a Static RAM. The write cycle is completely self-timed and initiated by a low going pulse on the \overline{WE} pin. On the falling edge of \overline{WE} , the address information is latched. On rising edge, the data and the control pins (\overline{CE} and \overline{OE}) are latched.

2.5 Data Polling

The 28C16A features Data polling to signal the completion of a byte write cycle. During a write cycle, an attempted read of the last byte written results in the data complement of I/O7 (I/O0 to I/O6 are indeterminate). After completion of the write cycle, true data is available. Data polling allows a simple read/compare operation to determine the status of the chip eliminating the need for external hardware.

2.6 Electronic Signature for Device Identification

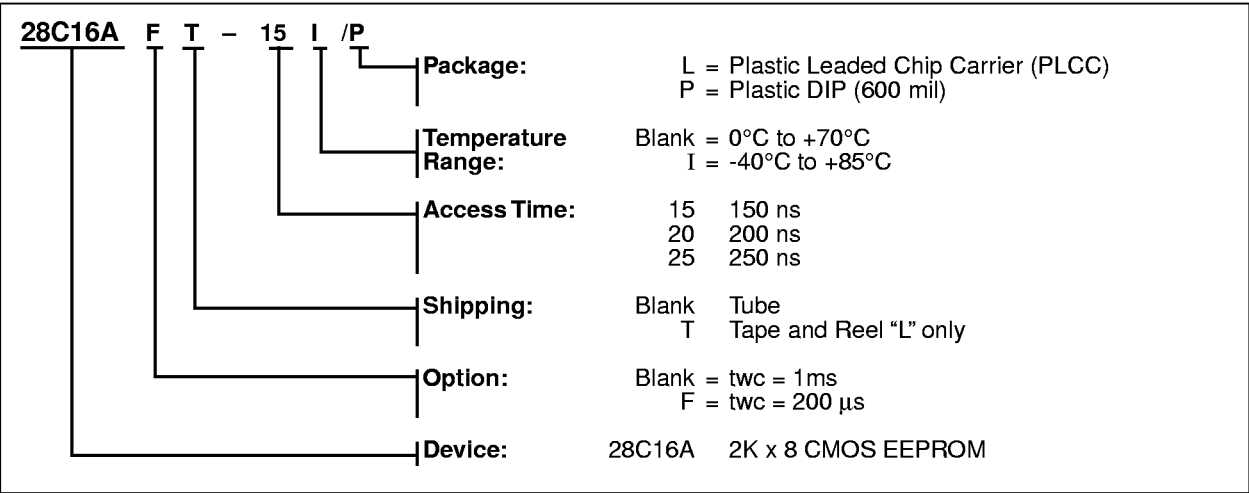
An extra row of 32 bytes of EEPROM memory is available to the user for device identification. By raising A9 to 12V $\pm 0.5V$ and using address locations 7E0 to 7FF, the additional bytes can be written to or read from in the same manner as the regular memory array.

2.7 Chip Clear

All data may be cleared to 1's in a chip clear cycle by raising \overline{OE} to 12 volts and bringing the \overline{WE} and \overline{CE} low. This procedure clears all data, except for the extra row.

28C16A Product Identification System

To order or to obtain information, e.g., on pricing or delivery, please use the listed part numbers, and refer to the factory or the listed sales offices.

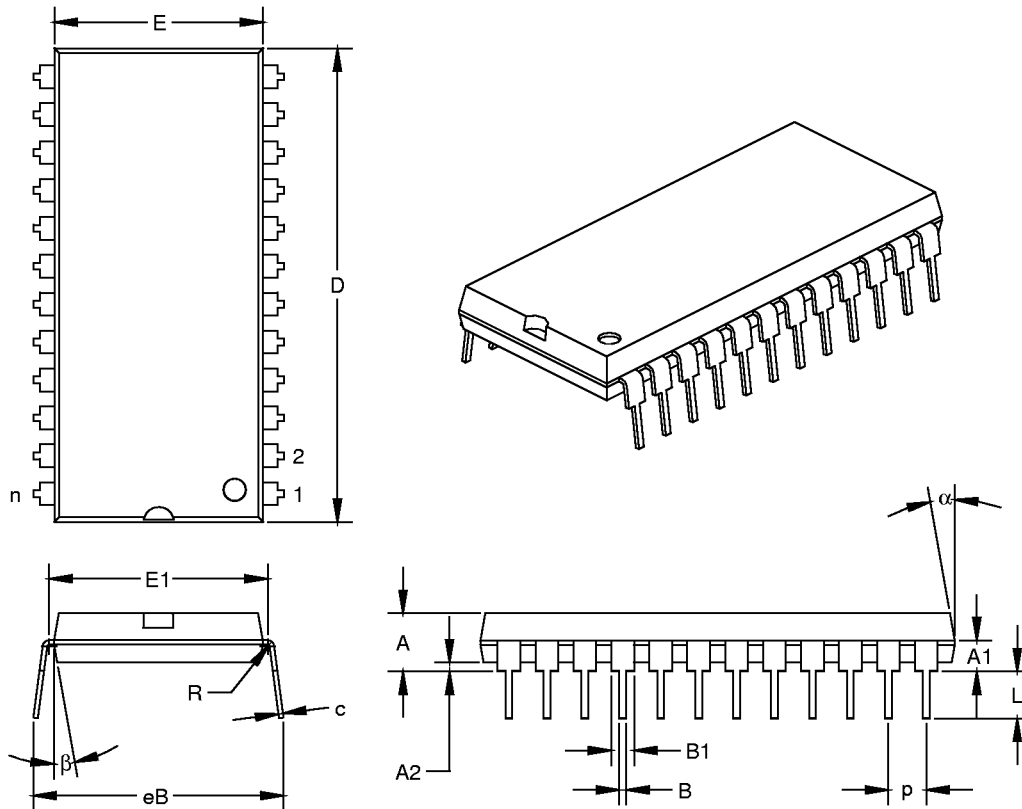




MICROCHIP

Packaging Diagrams and Parameters

Package Type: K04-081 24-Lead Plastic Dual In-line (P) – 600 mil



Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
PCB Row Spacing			0.600			15.24	
Number of Pins	n		24			24	
Pitch	p		0.100			2.54	
Lower Lead Width	B	0.014	0.018	0.022	0.36	0.46	0.56
Upper Lead Width	B1†	0.055	0.060	0.065	1.40	1.52	1.65
Shoulder Radius	R	0.000	0.005	0.010	0.00	0.13	0.25
Lead Thickness	c	0.008	0.012	0.015	0.20	0.29	0.38
Top to Seating Plane	A	0.140	0.165	0.190	3.56	4.19	4.83
Top of Lead to Seating Plane	A1	0.064	0.084	0.104	1.61	2.12	2.63
Base to Seating Plane	A2	0.020	0.025	0.030	0.51	0.64	0.76
Tip to Seating Plane	L	0.115	0.125	0.135	2.92	3.18	3.43
Package Length	D‡	1.245	1.250	1.255	31.62	31.75	31.88
Molded Package Width	E‡	0.540	0.550	0.560	13.72	13.97	14.22
Radius to Radius Width	E1	0.562	0.577	0.592	14.27	14.66	15.04
Overall Row Spacing	eB	0.630	0.660	0.690	16.00	16.76	17.53
Mold Draft Angle Top	α	5	10	15	5	10	15
Mold Draft Angle Bottom	β	5	10	15	5	10	15

* Controlling Parameter.

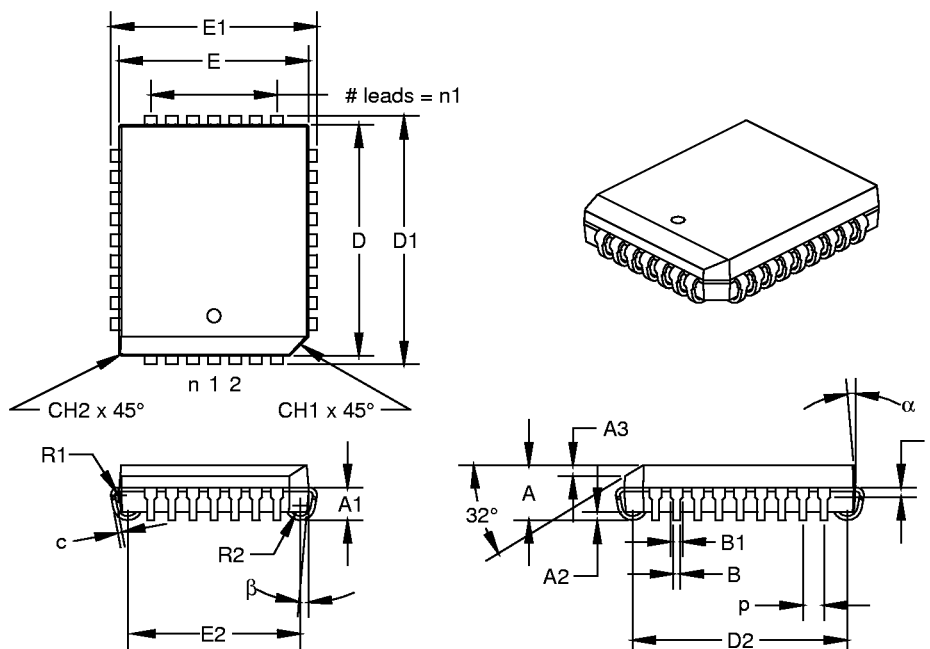
† Dimension "B1" does not include dam-bar protrusions. Dam-bar protrusions shall not exceed 0.003" (0.076 mm) per side or 0.006" (0.152 mm) more than dimension "B1."

‡ Dimensions "D" and "E" do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010" (0.254 mm) per side or 0.020" (0.508 mm) more than dimensions "D" or "E."

JEDEC equivalent: MS-011 AA

Packaging Diagrams and Parameters

Package Type: K04-023 32-Lead Plastic Leaded Chip Carrier (L) – Rectangle



Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		32			32	
Pitch	p		0.050			1.27	
Overall Pack. Height	A	0.127	0.131	0.135	3.23	3.33	3.43
Shoulder Height	A1	0.060	0.078	0.095	1.52	1.97	2.41
Standoff	A2	0.015	0.020	0.025	0.38	0.51	0.64
Side 1 Chamfer Dim.	A3	0.021	0.026	0.031	0.53	0.66	0.79
Corner Chamfer (1)	CH1	0.035	0.045	0.055	0.89	1.14	1.40
Corner Chamfer (other)	CH2	0.000	0.005	0.010	0.00	0.13	0.25
Overall Pack. Width	E1	0.485	0.490	0.495	12.32	12.45	12.57
Overall Pack. Length	D1	0.585	0.590	0.595	14.86	14.99	15.11
Molded Pack. Width	E [‡]	0.447	0.450	0.453	11.35	11.43	11.51
Molded Pack. Length	D [‡]	0.547	0.550	0.553	13.89	13.97	14.05
Footprint Width	E2	0.380	0.410	0.440	9.65	10.41	11.18
Footprint Length	D2	0.480	0.510	0.540	12.19	12.95	13.72
Pins along Width	n1		7			7	
Lead Thickness	c	0.008	0.010	0.012	0.20	0.25	0.30
Upper Lead Width	B1 [†]	0.026	0.029	0.032	0.66	0.74	0.81
Lower Lead Width	B	0.013	0.017	0.021	0.33	0.43	0.53
Upper Lead Length	L	0.010	0.020	0.030	0.25	0.51	0.76
Shoulder Inside Radius	R1	0.003	0.008	0.013	0.08	0.20	0.33
J-Bend Inside Radius	R2	0.020	0.025	0.030	0.51	0.64	0.76
Mold Draft Angle Top	α	0	5	10	0	5	10
Mold Draft Angle Bottom	β	0	5	10	0	5	10

* Controlling Parameter.

† Dimension "B1" does not include dam-bar protrusions. Dam-bar protrusions shall not exceed 0.003" (0.076 mm) per side or 0.006" (0.152 mm) more than dimension "B1."

‡ Dimensions "D" and "E" do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010" (0.254 mm) per side or 0.020" (0.508 mm) more than dimensions "D" or "E."

JEDEC equivalent: MS-016 AE